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(c) performing a lateral growth step which increases the thickness of said dielectric in proximity to sidewalls of said gate, but not under central regions of said gate;

(d) depositing a metallic material onto sidewalls of said gate;

(e) reacting said metallic material with said gate to form a conductive compound; and

(f) stripping unreacted portions of said metallic material; whereby a gate structure with enhanced conductivity is formed.

[Rewrite claim 9 as follows:]

9. (Amended) A product produced by the method [of Claim 6] for forming a transistor gate structure, comprising the steps of:

(a) forming a dielectric over a semiconductor region;

(b) forming a patterned gate over said dielectric;

(c) performing a lateral growth step which increases the thickness of said dielectric in proximity to sidewalls of said gate, but not under central regions of said gate;

(d) after said step (c), forming conductive sidewall spacers on said gate..

REMARKS

Claims 1 and 2 have been cancelled without prejudice, claims 8 and 9 have been rewritten to include the subject matter of the claims to which they refer and claims 3 to 7 are withdrawn from consideration. Accordingly, claims 8 and 9 remain active in this application.